

28. A method according to claim 27, said method further comprising:
disposing a transparent electrode comprising gold on the second clad layer; and
disposing an electrode pad on the first clad layer.

Control
B²
29. (Amended) A method according to claim 27, said method further comprising:
interposing a layer comprising $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}$ (including $X=0$, $Y=0$, $X=Y=0$) between
the light emitting layer and the second clad layer,
wherein said interposed layer has a wide band gap and is doped with an acceptor.

B³
32. (Amended) A method according to claim 27, said method further comprising:
growing the layers as crystals by a metal organic vapor phase epitaxial growth
method with nitrogen, ammonia and alkyl compound gases containing a group III element.

Please see the attached Appendix for the changes made to effect the above claims.